ABSTRACT

MANUFACTURE OF SEMICONDUCTOR DEVICES

A method of manufacturing a semiconductor device comprises forming a plurality of openings (9e, 9b, 9c) for ohmic contact portions at the same time, then forming a semiconductor layer (11) on an entire surface including the openings, and selectively introducing impurities by ion implantation into the contact portions and isolated other element regions (11e, 11b, 11c, 11t, 11R) of the semiconductor layer (11), thereby producing a transistor (Tr) and at least one other element (R; R, C).

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